

15

✓ High class but terrible quality

14 and (ONO or (charge ad trapping ad dielectric))

 025 1000 1000 1000 1000 1000

	U	I	PT	F	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C	N	A	P
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040140510	20040722	21	Semiconductor memory device having a gate in-	257/390	257/261; 257/324;		Hazama, Hiroaki	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020047163	20020425	52	Semiconductor device and SOI substrate	257/410	257/E21.19 3;		Kunikiyo, Tatsuya	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6740605	20040525	15	Process for reducing hydrogen contamination	438/795	438/471; 438/473;		Shiraiwa, Hidehiko et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	B1 US 6677213	20040113	11	SOMOS structure including a deuterated	438/308	438/795		Ramkumar, Krishnaswamy et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	B1 US 6670241	20031230	9	Semiconductor memory with deuterated materia	438/258			Ramal, Tazrien et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	B2 US 6661065	20031209	50	Semiconductor device and SOI substrate	257/411	257/347; 257/510;		Kunikiyo, Tatsuya	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>